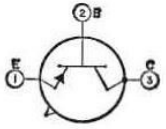
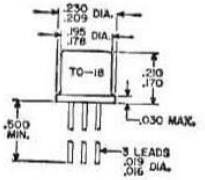
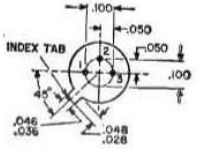
TRANSISTOR

2N962

Germanium p-n-p type used in high-speed saturated switching applications in industrial data-processing equipment. JEDEC No. TO-18 package; outline 12, Outlines Section.







MAXIMUM RATINGS

Collector-to-Base Voltage	−12 max	volts
Collector-to-Emitter Voltage (with external base-to-emitter resistance = 0)	−12 max	volts
Collector-to-Emitter Voltage	−7 max	volts
Emitter-to-Base Voltage	−1.25 max	volts
Collector Current	−100 max	ma
Transistor Dissipation:		
At case temperatures up to 25°C	300 max	mw
At ambient temperatures up to 25°C	150 max	mw
At case or ambient temperatures above 25°C	See curve page 80	
Temperature Range:		
Operating	−55 to 100	°C
Storage	−65 to 100	°C
Lead Temperature (for 10 seconds maximum)	230 max	°C

CHARACTERISTICS

Collector-to-Emitter Saturation Voltage:		
With collector ma = −10 and base ma = −1	−0.2 max	volt
With collector ma = −50 and base ma = −5	−0.4 max	volt
With collector ma = −100 and base ma = −10	−0.7 max	volt
Collector-Cutoff Current (with collector-to-base volts = −6 and emitter current = 0)	−3 max	μa
In Common-Base Circuit		
Emitter-to-Base Capacitance (with emitter-to-base volts = −1, collector current = 0, and frequency = 100 kc)	3.5 max	pf
Collector-to-Base Capacitance (with collector-to-base volts = −10, emitter current = 0, and frequency = 1 Mc)	4 max	pf
Gain-Bandwidth Product (with collector-to-base volts = −1, emitter current = 20, and frequency = 100 Mc)	300 min	Mc
In Common-Emitter Circuit		
DC Forward Current-Transfer Ratio:		
With collector-to-emitter volts = −0.3 and collector ma = −10	20 min	
With collector-to-emitter volts = −1 and collector ma = −50	20 min	
With collector-to-emitter volts = −1 and collector ma = −100	20 min	